

**Amendments to the Claims:**

1-6 (Canceled)

7. (New) A semiconductor device comprising:

an active device provided in a semiconductor substrate facing its principal plane,

a contact electrode provided outside of the semiconductor substrate conducting with the active device,

a P-type body region disposed in the active device,

a drift region of N-type semiconductor provided below the P-type body region,

a region of P-type semiconductor provided contacting the drift region and below the drift region, and

a gate electrode insulated from the semiconductor substrate,

wherein an end portion of contacting portion of the active device to the contact electrode is composed with P-type semiconductor, and a corner of the end portion on the P-type region of the active device is formed with a curved line or with an obtuse angle.

8. (New) A semiconductor device of claim 7,

wherein a plurality of active devices are discretely arranged in the semiconductor substrate, and each active device has a contacting portion to a contact electrode, and

a corner portion of a contacting portion of an active device positioned at the end and at opposite side to another active device is formed with a curved line or with an obtuse angle.

9. (New) A semiconductor device of claim 7,

wherein the shape of contacting portion of the active device to the contact electrode is formed in a broader width in an end portion than in the central portion.

10. (New) A semiconductor device of claim 9,

wherein a plurality of active devices are discretely arranged in the

semiconductor substrate, and each active device has a contacting portion to a contact electrode,

an end portion of a contacting portion of an active device positioned at an end and at opposite side of another active device is formed broader than the central portion of the contacting portion, and

a corner portion of the end portion is formed with a curved line or with an obtuse angle.

11. (New) A semiconductor device comprising:

an active device provided in a semiconductor substrate facing its principal plane,

a contact electrode provided outside of the semiconductor substrate conducting with the active device,

a P-type body region disposed in the active device ,

a drift region of N-type semiconductor provided below the P-type body region,

a region of P-type semiconductor provided contacting the drift region and below the drift region, and

a gate electrode insulated from the semiconductor substrate,

wherein an end portion of contacting portion of the active device to the contact electrode is composed with P-type semiconductor, and impurity concentration within the contacting portion is lower at a corner portion of contacting portion than in other portion of it.

12. (New) A semiconductor device of claim 11,

wherein a plurality of active devices are discretely arranged in the semiconductor substrate, and each active device has a contacting portion to a contact electrode, and

a corner portion of a contacting portion of an active device positioned at an end and at opposite side of another active device is lower in impurity concentration than other portion of the contacting portion.